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(54) Title: SUBSTRATE COMPRISING DIFFERENT TYPES OF SURFACES AND METHOD FOR OBTAINING SUCH SUBSTRATES

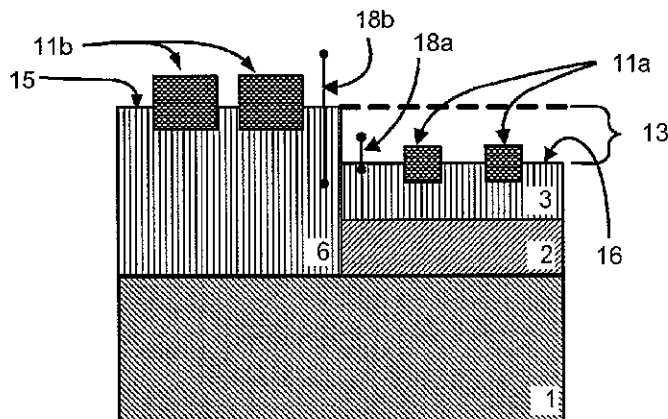


Figure 15

(57) Abstract: A support having a larger density of crystalline defects, an insulating layer disposed on a first region of a front face of the support, and a superficial layer disposed on the insulating layer. An additional layer can be disposed at least on a second region of the front face of the support has a thickness sufficient to bury crystalline defects of the support. A substrate can also include an epitaxial layer arranged at least over the first region of the front face of the support, between the support and the insulation layer. Also, a method of making the substrate by forming a masking layer on the first region of the superficial layer and removing the superficial layer and the insulating layer in the second region uncovered by the masking layer. The additional layer is formed in the second region and then planarized.

